International
IOR Rectifier

Preliminary Data SheetPD - 9.760

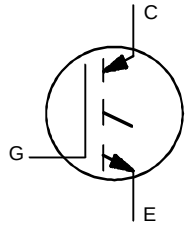
IRGPH50S

INSULATED GATE BIPOLAR TRANSISTOR

Standard Speed IGBT

Features

- Switching-loss rating includes all "tail" losses
- Optimized for line frequency operation (to 400Hz) See Fig. 1 for Current vs. Frequency curve



n-channel

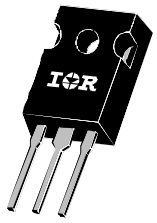
V_{CES} = 1200V

$V_{CE(sat)} \leq 2.0V$

@V_{GE} = 15V, I_C = 33A

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.



TO-247AC

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
I_C @ T_C = 25°C	Continuous Collector Current	57	A
I_C @ T_C = 100°C	Continuous Collector Current	33	
I_{CM}	Pulsed Collector Current ①	110	
I_{LM}	Clamped Inductive Load Current ②	110	
V_{GE}	Gate-to-Emitter Voltage	±20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	20	mJ
P_D @ T_C = 25°C	Maximum Power Dissipation	200	W
P_D @ T_C = 100°C	Maximum Power Dissipation	78	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.64	°C/W
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6 (0.21)	—	g (oz)

Revision 0

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	V_{GE} = 0V, I_C = 250µA
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	20	—	—	V	V_{GE} = 0V, I_C = 1.0A
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.3	—	V/°C	V_{GE} = 0V, I_C = 1.0mA
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.7	2.0	V	I_C = 33A V_{GE} = 15V
		—	2.2	—		I_C = 57A See Fig. 2, 5
		—	2.0	—		I_C = 33A, T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		V_{CE} = V_{GE}, I_C = 250µA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-13	—	mV/°C	V_{CE} = V_{GE}, I_C = 250µA
g_{fe}	Forward Transconductance ⑤	—	19	—	S	V_{CE} = 100V, I_C = 33A
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	µA	V_{GE} = 0V, V_{CE} = 1200V
		—	—	1000		V_{GE} = 0V, V_{CE} = 1200V, T_J = 150°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	72	108		I_C = 33A
Q_{ge}	Gate - Emitter Charge (turn-on)	—	16	24	nC	V_{CC} = 400V See Fig. 8
Q_{gc}	Gate - Collector Charge (turn-on)	—	19	30		V_{GE} = 15V
$t_{d(on)}$	Turn-On Delay Time	—	62	—		T_J = 25°C
t_r	Rise Time	—	77	—	ns	I_C = 33A, V_{CC} = 960V
$t_{d(off)}$	Turn-Off Delay Time	—	1200	1800		V_{GE} = 15V, R_G = 5.0Ω
t_f	Fall Time	—	780	1200		Energy losses include "tail"
E_{on}	Turn-On Switching Loss	—	3.0	—		
E_{off}	Turn-Off Switching Loss	—	26	—	mJ	See Fig. 9, 10, 11, 14
E_{ts}	Total Switching Loss	—	29	44		
$t_{d(on)}$	Turn-On Delay Time	—	52	—		T_J = 150°C,
t_r	Rise Time	—	76	—	ns	I_C = 33A, V_{CC} = 960V
$t_{d(off)}$	Turn-Off Delay Time	—	1300	—		V_{GE} = 15V, R_G = 5.0Ω
t_f	Fall Time	—	2100	—		Energy losses include "tail"
E_{ts}	Total Switching Loss	—	55	—	mJ	See Fig. 10, 14
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	1900	—		V_{GE} = 0V
C_{oes}	Output Capacitance	—	140	—	pF	V_{CC} = 30V See Fig. 7
C_{res}	Reverse Transfer Capacitance	—	24	—		f = 1.0MHz

Notes:

① Repetitive rating; V_{GE}=20V, pulse width limited by max. junction temperature. (See fig. 13b)

② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10µH, R_G= 5.0Ω, (See fig. 13a)

③ Repetitive rating; pulse width limited by maximum junction temperature.

④ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

⑤ Pulse width 5.0µs, single shot.

Refer to Section D - page D-13

Package Outline 3 - JEDEC Outline TO-247AC (TO-3P)